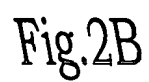
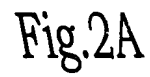


Fig.1



3/19

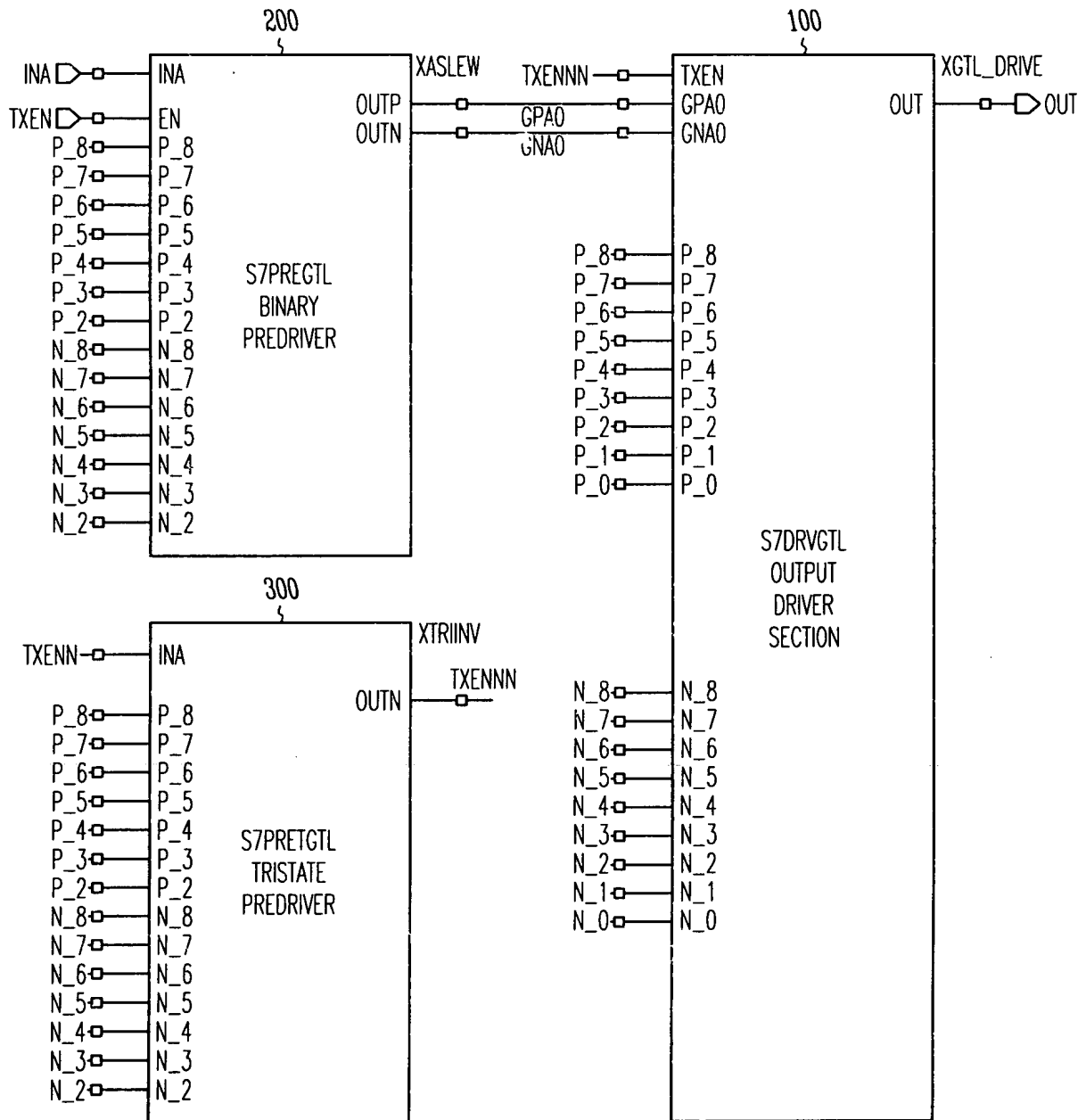
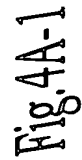


Fig.3



5/19



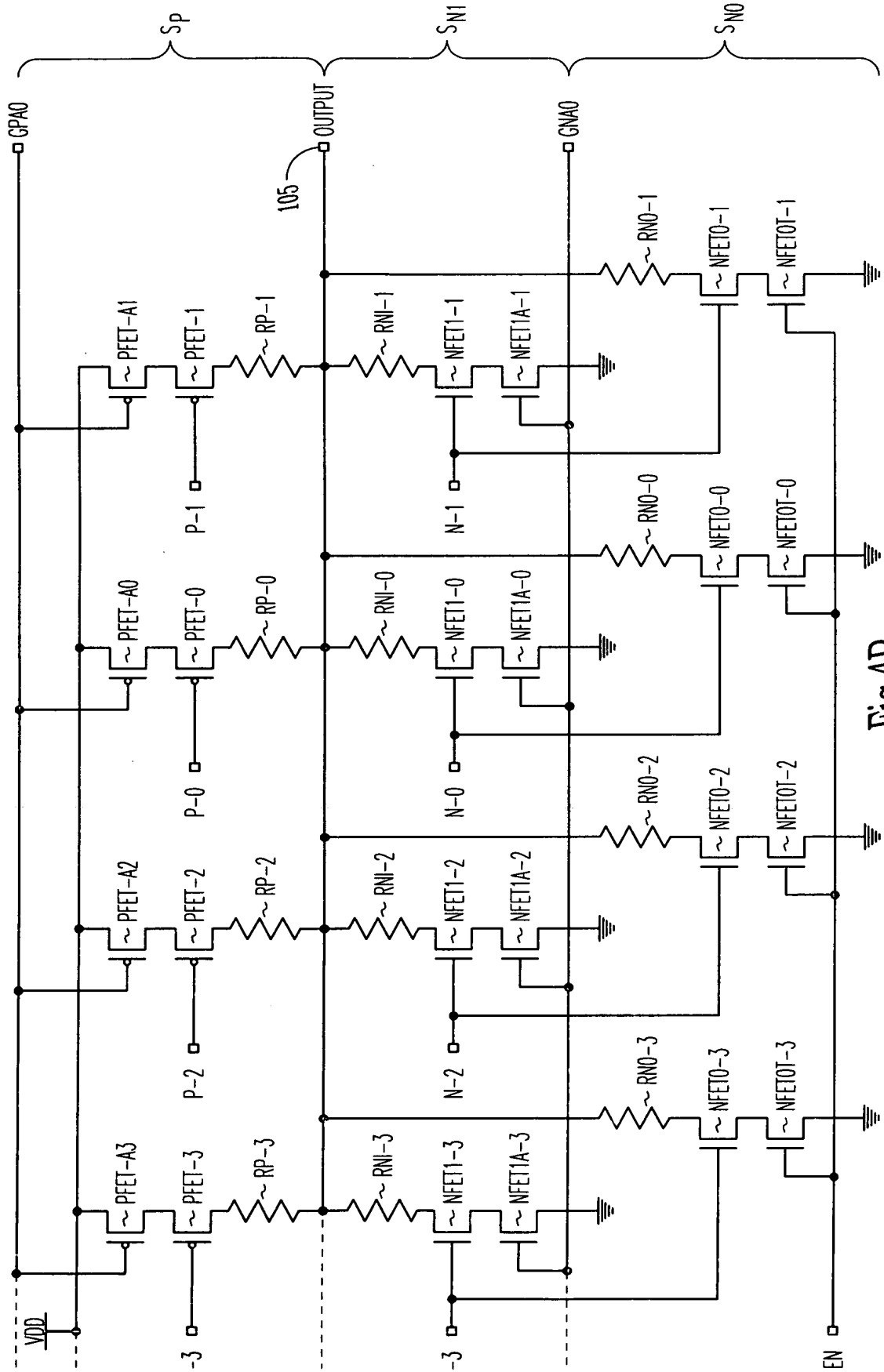
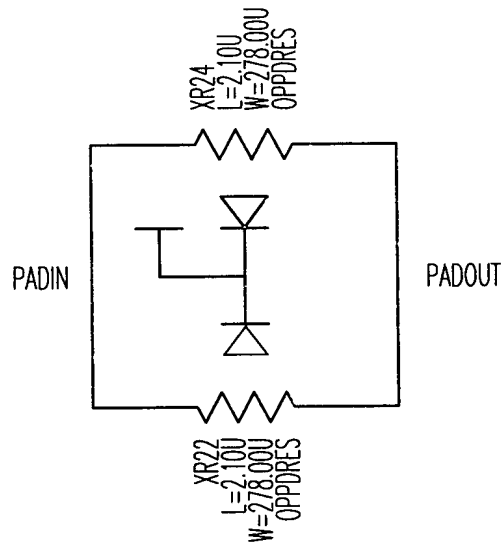


Fig.4B

TITLE: GTL + DRIVER
INVENTORS NAME: Rodney Ruesch
SERIAL NO.: 09/620,679

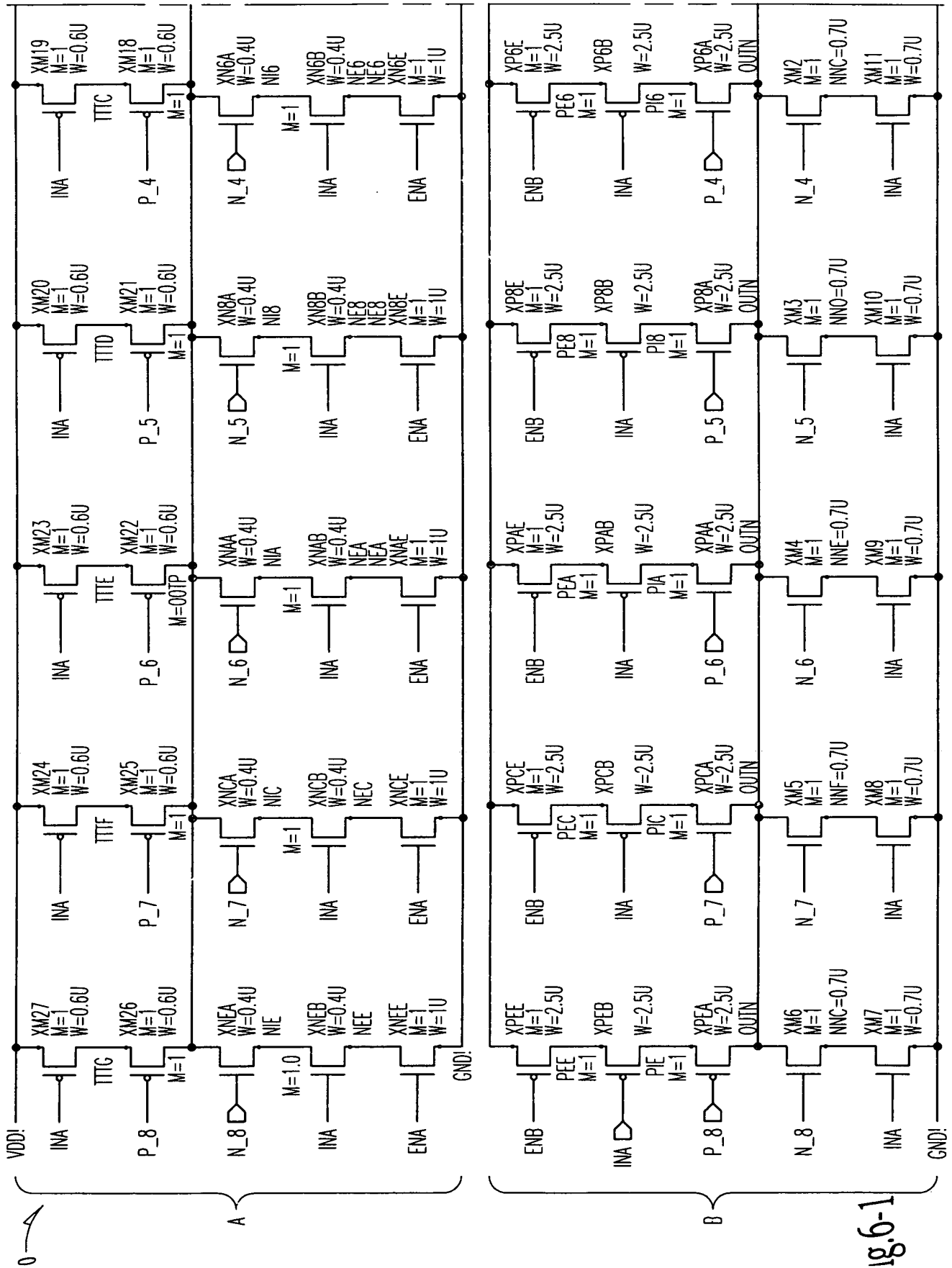
7/19

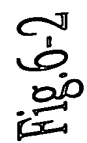


SELECTABLE OP RESISTORS TO BE USED WITH PADXFER METAL (LM) TOTAL RESISTANT MATCHING UP TO 3 OHMS

ONE RESISTOR L=2.1U AND W=93.0U = 3.0 OHMS
ONE RESISTOR L=2.1U AND W=111.0U = 2.5 OHMS
ONE RESISTOR L=2.1U AND W=139.0U = 2.0 OHMS
ONE RESISTOR L=2.1U AND W=185.0U = 1.5 OHMS
ONE RESISTOR L=2.1U AND W=278.0U = 1.0 OHMS
TWO RESISTORS L=2.1U AND W=278.0U IN PARALLEL = 0.5 OHMS SHOWN
ZERO RESISTORS TO BE USED FOR 0 OHMS

Fig.5





10/19

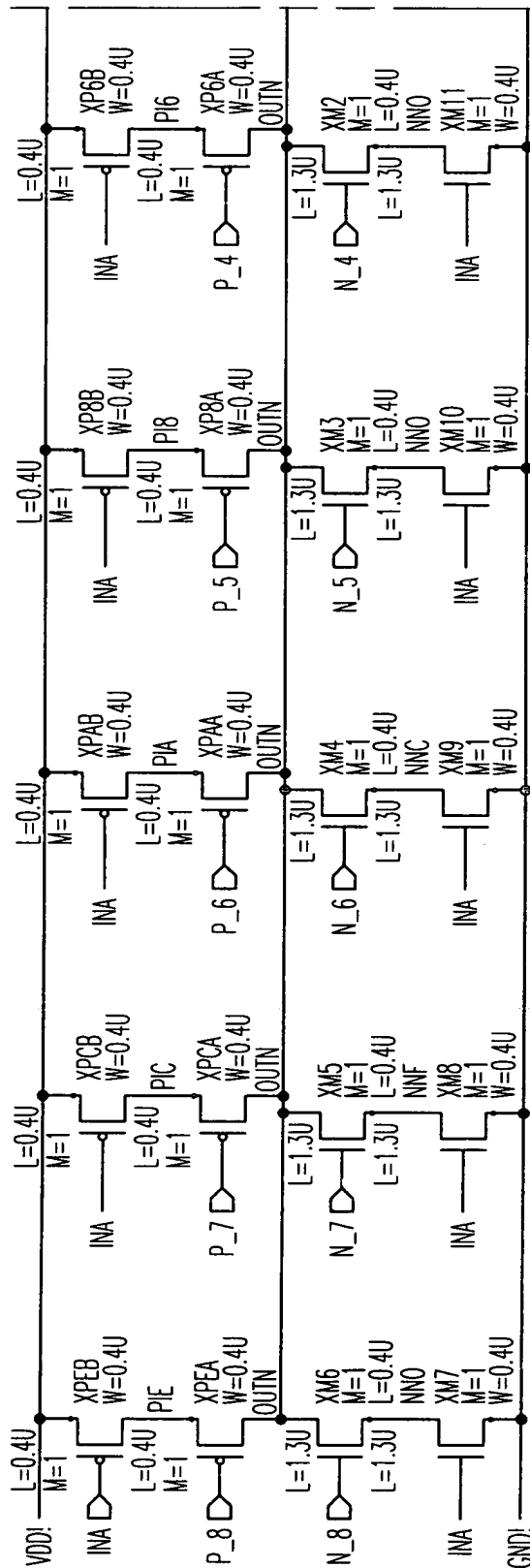


Fig.7-1

11/19

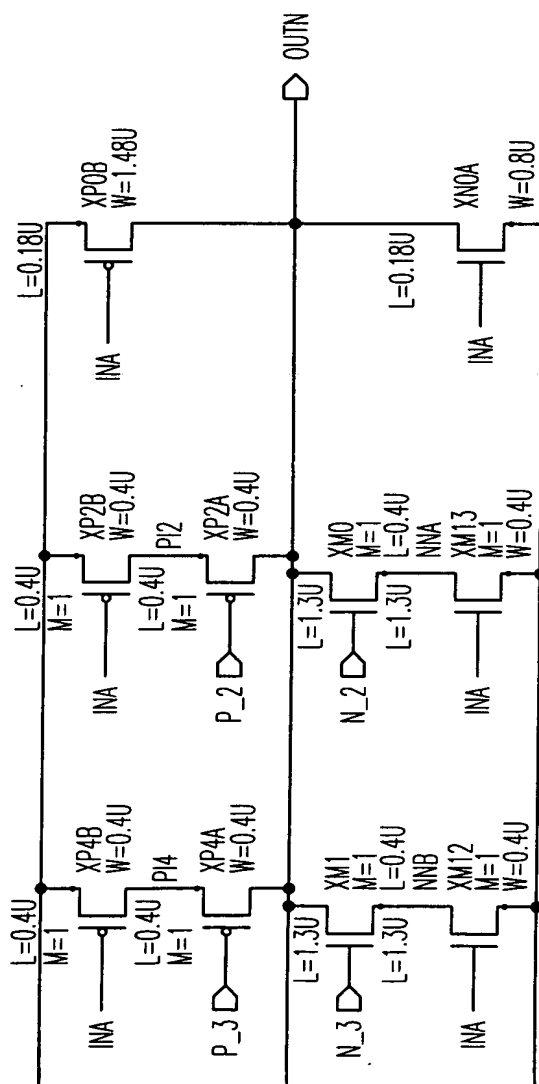


Fig. 7-2

12/19

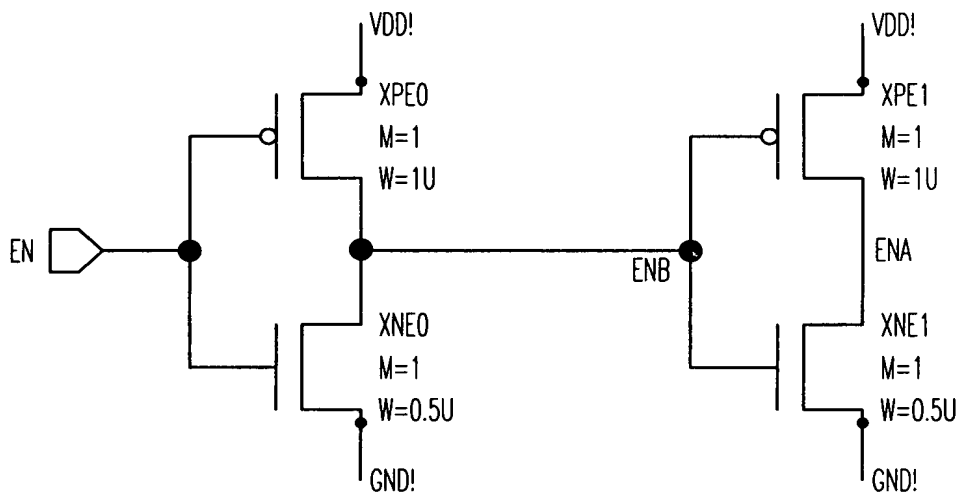
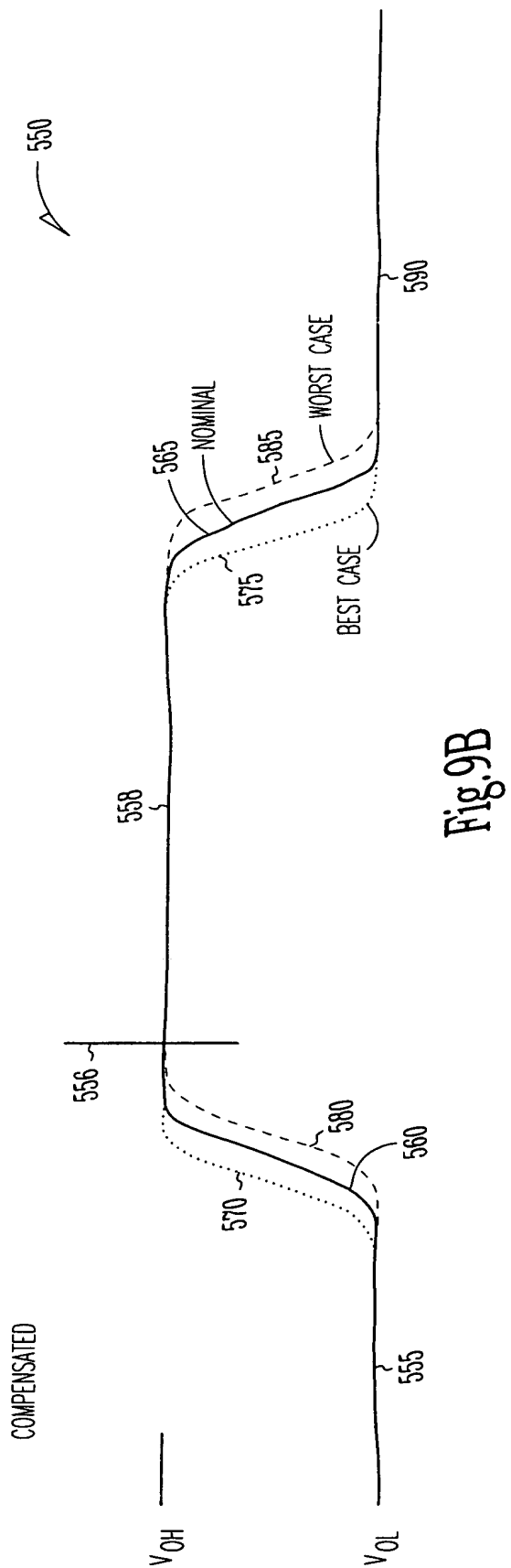
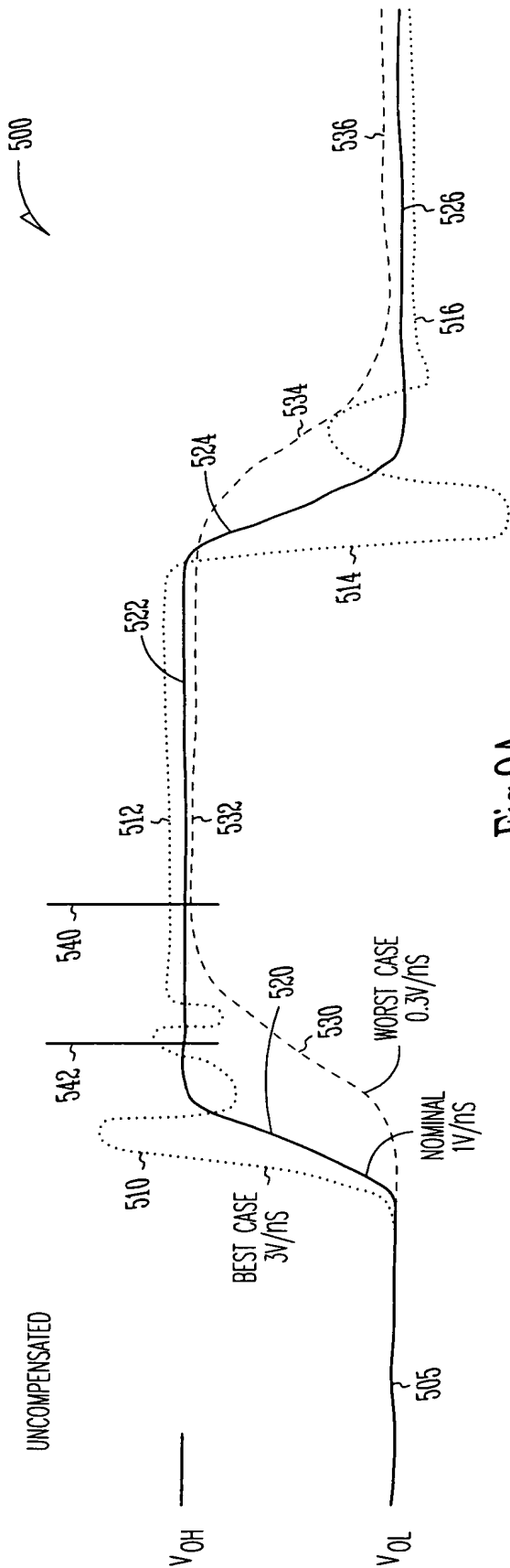


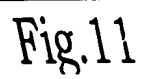
Fig.8



NON-INVERTING BI-DIRECTIONAL DRIVER/RECEIVER THAT INTERFACES 1.8V INTERNAL FUNCTIONS WITH 1.1V ENHANCED GTL+ OFF-CHIP BI-DIRECTIONAL DATA BUS. THE DRIVER OPERATES WITH A 1.8V SUPPLY. THE DRIVER HAS OFF-CHIP TERMINATION OF 45 OHM TO 1.1V (V_{TT}) AT EACH END OF THE BUS (DOUBLE TERMINATION). THE RECEIVER HAS EXTERNAL REFERENCE V_{ref} ($V_{TT} * 2/3$).

Fig.10

15/19



16/19

DRIVER TRUTH TABLE

INPUTS					OUTPUTS			
A0	A1	SA	TS	DI	PVTP	PVTN	PAD	COMMENTS
-	-	-	0	-	-	-	HI-Z ¹	HIGH IMPEDANCE MODE
-	-	-	-	0	-	-	HI-Z ¹	HIGH IMPEDANCE MODE
-	-	-	-	-	0 ²	0 ²	HI-Z ¹	PVT TEST MODE
0	-	0	-	-	-	0 ²	HI-Z ¹	PVT TEST MODE
1	-	0	-	-	0 ²	-	HI-Z ¹	PVT TEST MODE
0	-	0	1	1	-	>0	0 ³	PVT TEST MODE ³
1	-	0	1	1	>0	-	1 ³	PVT TEST MODE ³
0	-	0	1	1	>0	>0	0 ³	FUNCTIONAL, A0 DATA MODE
0	-	0	1	1	1	1	0 ³	FUNCTIONAL, 10 OHMS @ BC
0	-	0	1	1	4	4	0 ³	FUNCTIONAL, 10 OHMS @ NOM
0	-	0	1	1	8	8	0 ³	FUNCTIONAL, 10 OHMS @ WC
1	-	0	1	1	>0	>0	1 ³	FUNCTIONAL, A0 DATA MODE
-	-	1	1	1	>0	>0	A1	FUNCTIONAL, A1 DATA MODE

1. PAD IS AT "V_{TT}" WHEN CONNECTED TO OFF-CHIP TERMINATOR.

2. WHEN PVT=0 ALL PVT BITS GO TO V_{SS} AND ARE OFF.

3. PAD LOGICAL "1" = V_{HT} = 1.1V, LOGICAL "0" = 0.4V OR LESS.

NOTES: A. V_{dd} = 1.8(+/-0.1)V, V_{HT} = 1.1(+/-0.02)V

B. DURING MODULE EXTERNAL I/O TEST AND SYSTEM MODE, DRIVER OUTPUT PULLUP IS MADE

BY THE EXTERNAL 22.5 OHM RESISTOR TO V_{HT}.

C. NDR WILL BE BASED ON DRIVER TERMINATED OFF-CHIP.

D. A0, A1, AN0, AND AN1 ARE INDEPENDENT FROM EACH OTHER.

E. ENTRIES IN COLUMNS PVTP, PVTN REPRESENT NUMBER OF LINES HELD AT LOGIC "1"

STATE. FOR TESTING, THE IMPEDANCE CONTROLLER FORCES PVTP AND PVTN TO 4

(i.e. PVTP[8:0] = PVTN[8:0] = [000011110]) FOR ALL SUPPLY VOLTAGE LEVELS.

Fig.12

17/19

DRIVER TRUTH TABLE

INPUTS						OUTPUT		
AN0	AN1	SA	TSN	DI	PVTP	PVTN	PADN	COMMENTS
-	-	-	0	-	-	-	HI-Z ¹	HIGH IMPEDANCE MODE
-	-	-	-	0	-	-	HI-Z ¹	HIGH IMPEDANCE MODE
-	-	-	-	-	0 ²	0 ²	HI-Z ¹	PVT TEST MODE
0	-	0	-	-	-	0 ²	HI-Z ¹	PVT TEST MODE
1	-	0	-	-	0 ²	-	HI-Z ¹	PVT TEST MODE
0	-	0	1	1	-	>0	0 ³	PVT TEST MODE ³
1	-	0	1	1	>0	-	1 ³	PVT TEST MODE ³
0	-	0	1	1	>0	>0	0 ³	FUNCTIONAL, A0 DATA MODE
0	-	0	1	1	1	1	0 ³	FUNCTIONAL, 10 OHMS @ BC
0	-	0	1	1	4	4	0 ³	FUNCTIONAL, 10 OHMS @ NOM
0	-	0	1	1	8	8	0 ³	FUNCTIONAL, 10 OHMS @ WC
1	-	0	1	1	>0	>0	1 ³	FUNCTIONAL, A0 DATA MODE
-	-	1	1	1	>0	>0	A1	FUNCTIONAL, A1 DATA MODE

1. PAD IS AT "V_{TT}" WHEN CONNECTED TO OFF-CHIP TERMINATOR.

2. WHEN PVT=0 ALL PVT BITS GO TO V_{SS} AND ARE OFF.

3. PAD LOGICAL "1"=V_{TT}=1.1V, LOGICAL "0"=0.4V OR LESS.

NOTES: A. V_{dd}=1.8(+/-0.1)V, V_{TT}=1.1(+/-0.02)V

B. DURING MODULE EXTERNAL I/O TEST AND SYSTEM MODE, DRIVER OUTPUT PULLUP IS MADE

BY THE EXTERNAL 22.5 OHM RESISTOR TO V_{TT}.

C. NDR WILL BE BASED ON DRIVER TERMINATED OFF-CHIP.

D. A0, A1, AN0, AND AN1 ARE INDEPENDENT FROM EACH OTHER.

E. ENTRIES IN COLUMNS PVTP, PVTN REPRESENT NUMBER OF LINES HELD AT LOGIC "1" STATE. FOR TESTING, THE IMPEDANCE CONTROLLER FORCES PVTP AND PVTN TO 4 (i.e. PVTP[8:0]=PVTN[8:0]=[000011110]) FOR ALL SUPPLY VOLTAGE LEVELS.

Fig.13

18/19

RIVER PROPAGATION DELAYS (NO LOAD ON OUTPUTS)			DELAY (ns)=INTERCEPT+SLOPE (D _{std}) ¹		
PATH (INPUT TO OUTPUT)	PERFORMANCE LEVEL	PARAMETER	V _{dd} =1.72V V _{tt} =1.08V T _j =100°C PROCESS=SLOW	V _{dd} =1.8V V _{tt} =1.13V T _j =60°C PROCESS=NOM.	V _{dd} =1.92V V _{tt} =1.12V T _j =25°C PROCESS=FAST
AO-PAD	A	t _{PLH}	1.2ns	1.0ns	0.8ns
		t _{PHL}	1.2ns	1.0ns	0.8ns
ANO-PADN	A	t _{PLH}	1.2ns	1.0ns	0.8ns
		t _{PHL}	1.2ns	1.0ns	0.8ns

1. D_{std} IS THE NUMBER OF STANDARD LOADS.
2. VOLTAGE AT THE PACKAGE PIN.
3. DESIGN IS OPTIMIZED FOR V_{tt}=1.1V, CAN BE USED FOR V_{tt}=1.0V TO 1.2V.

Fig.14

19/19

